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SJ

**INDUSTRY STANDARD OF THE
PEOPLE'S REPUBLIC OF CHINA**

SJ/T 11227-2000

Replacing SJ 1410-1978

**Detail specification for electronic components Type 3DA98 NPN
silicon high-frequency power transistor**

电子元器件详细规范 3DA98型NPN硅高频大功率晶体管
(English Translation)

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What this standard covers

This standard applies to 3DA98 type silicon high-power transistor, which is in accordance with GB/T 7576-1998 "Semiconductor devices Discrete devices Part 7 bipolar transistors fourth frequency amplification Case rated bipolar transistors for Blank detail specification "Standard for the former Ministry of the underlying SJ 1410-78" 3DA98 frequency power silicon NPN transistor "be revised, in line with GB/T 4589. 1-1989" Semiconductor devices Discrete devices and integrated circuits norms "and GB/T 12560-1999 "Semiconductor devices Discrete devices specification" Class ?? requirements. This specification referenced standards GB/T 4587-1994 "Discrete semiconductor devices and integrated circuits Part 7 bipolar transistors", GB/T 4589. 1-1989 "Semiconductor devices Discrete devices and integrated circuits norms", GB/T 4937 -1995 "Semiconductor devices Mechanical and climatic test methods" and GJB 128A-97 "Test Method for discrete semiconductor devices. "

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